



LCP1521

A.S.D.™

PROGRAMMABLE TRANSIENT VOLTAGE SUPPRESSOR FOR SLIC PROTECTION

FEATURES

- Dual programmable transient suppressor
- Wide negative firing voltage range:
 $V_{MGL} = -150 \text{ V max.}$
- Low dynamic switching voltages: V_{FP} and V_{DGL}
- Low gate triggering current: $I_{GT} = 5 \text{ mA max}$
- Peak pulse current: $I_{PP} = 30 \text{ A (10/1000 } \mu\text{s)}$
- Holding current: $I_H = 150 \text{ mA min}$

DESCRIPTION

This device has been especially designed to protect new high voltage, as well as classical SLICs, against transient overvoltages.

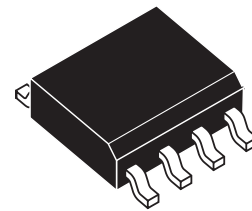
Positive overvoltages are clamped by 2 diodes. Negative surges are suppressed by 2 thyristors, their breakdown voltage being referenced to $-V_{BAT}$ through the gate.

This component presents a very low gate triggering current (I_{GT}) in order to reduce the current consumption on printed circuit board during the firing phase.

A particular attention has been given to the internal wire bonding. The Kelvin method configuration ensures reliable protection, reducing the overvoltage introduced by the parasitic inductances of the wiring, especially for very fast transients.

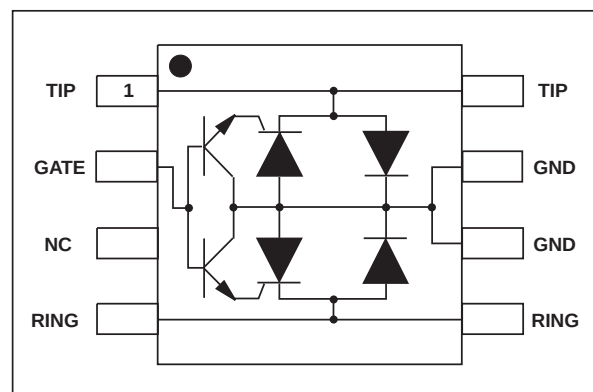
BENEFITS

Trisils are not subject to ageing and provide a fail safe mode in short circuit for a better protection. Trisils are used to help equipment to meet various standards such as UL1950, IEC950 / CSA C22.2, UL1459 and FCC part68. Trisils have UL94 V0 resin approved (Trisils are UL497B approved (file: E136224)).



SO-8

FUNCTIONAL DIAGRAM



IN COMPLIANCES WITH THE FOLLOWING STANDARDS

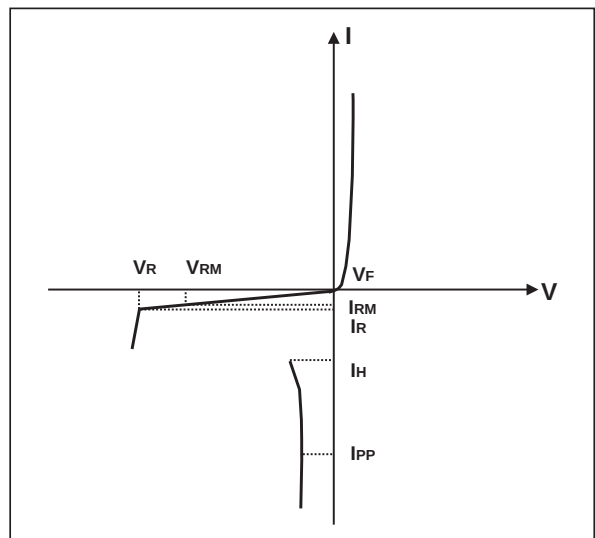
STANDARD	Peak Surge Voltage (V)	Voltage Waveform	Required peak current (A)	Current Waveform	Minimum serial resistor to meet standard (Ω)
GR-1089 Core First level	2500 1000	2/10 μ s 10/1000 μ s	500 100	2/10 μ s 10/1000 μ s	10 24
GR-1089 Core Second level	5000	2/10 μ s	500	2/10 μ s	20
GR-1089 Core Intra-building	1500	2/10 μ s	100	2/10 μ s	0
ITU-T-K20/K21	6000 1500	10/700 μ s	150 37.5	5/310 μ s	110 0
ITU-T-K20 (IEC61000-4-2)	8000 15000	1/60 ns	ESD contact discharge ESD air discharge		0 0
VDE0433	4000 2000	10/700 μ s	100 50	5/310 μ s	60 10
VDE0878	4000 2000	1.2/50 μ s	100 50	1/20 μ s	0 0
IEC61000-4-5	4000 4000	10/700 μ s 1.2/50 μ s	100 100	5/310 μ s 8/20 μ s	60 0
FCC Part 68, lightning surge type A	1500 800	10/160 μ s 10/560 μ s	200 100	10/160 μ s 10/560 μ s	22.5 15
FCC Part 68, lightning surge type B	1000	9/720 μ s	25	5/320 μ s	0

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-a)	Junction to ambient	170	°C/W

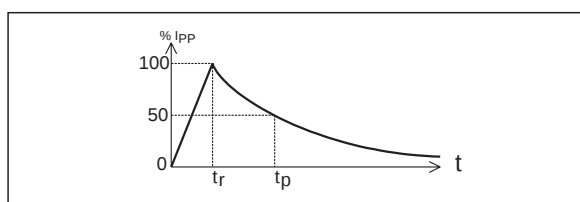
ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter
I _{GT}	Gate triggering current
I _H	Holding current
I _{RM}	Reverse leakage current LINE / GND
I _{RG}	Reverse leakage current GATE / LINE
V _{RM}	Reverse voltage LINE / GND
V _{GT}	Gate triggering voltage
V _F	Forward drop voltage LINE / GND
V _{FP}	Peak forward voltage LINE / GND
V _{DGL}	Dynamic switching voltage GATE / LINE
V _{GATE}	GATE / GND voltage
V _{RG}	Reverse voltage GATE / LINE
C	Capacitance LINE / GND



ABSOLUTE RATINGS ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified).

Symbol	Parameter		Value	Unit
I_{PP}	Peak pulse current (see note1)	10/1000 μs 8/20 μs 10/560 μs 5/310 μs 10/160 μs 1/20 μs 2/10 μs	30 100 35 40 50 100 170	A
I_{TSM}	Non repetitive surge peak on-state current (50Hz sinusoidal)	$t = 10\text{ms}$ $t = 1\text{s}$	20 5	A
I_{GSM}	Maximum gate current (50Hz sinusoidal)	$t = 10\text{ms}$	2	A
V_{MLG} V_{MGL}	Maximum voltage LINE/GND Maximum voltage GATE/LINE	$-40^{\circ}\text{C} < T_{amb} < +85^{\circ}\text{C}$ $-40^{\circ}\text{C} < T_{amb} < +85^{\circ}\text{C}$	-150 -150	V
T_{stg} T_j	Storage temperature range Maximum junction temperature		- 55 to + 150 150	$^{\circ}\text{C}$
T_L	Maximum lead temperature for soldering during 10s		260	$^{\circ}\text{C}$

Repetitive peak pulse currenttr: rise time (μs)tp: pulse duration (μs)ex: Pulse waveform 10/1000 μs tr = 10 μs tp = 1000 μs **1- PARAMETERS RELATED TO THE DIODE LINE / GND** ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Test conditions		Max	Unit
V_F	$I_F = 5\text{A}$	$t = 500\mu\text{s}$	2	V
V_{FP} (note 1)	10/700 μs 1.2/50 μs 2/10 μs	1.5kV 1.5kV 2.5kV $R_s = 10\Omega$ $R_s = 10\Omega$ $R_s = 62\Omega$	5 7 12	V

Note 1: see test circuit for V_{FP} ; R_s is the protection resistor located on the line card.

2 - PARAMETERS RELATED TO THE PROTECTION THYRISTOR ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test conditions		Min	Max	Unit
I_{GT}	$V_{GND/LINE} = -48\text{V}$		0.1	5	mA
I_H	$V_{GATE} = -48\text{V}$ (note 2)		150		mA
V_{GT}	at I_{GT}			2.5	V
I_{RG}	$V_{RG} = -150\text{V}$ $V_{RG} = -150\text{V}$	$T_c = 25^{\circ}\text{C}$ $T_c = 85^{\circ}\text{C}$		5 50	μA
V_{DGL}	$V_{GATE} = -48\text{V}$ (note 3) 10/700 μs 1.5kV $R_s = 10\Omega$ $I_{pp} = 30\text{A}$ 1.2/50 μs 1.5kV $R_s = 10\Omega$ $I_{pp} = 30\text{A}$ 2/10 μs 2.5kV $R_s = 62\Omega$ $I_{pp} = 38\text{A}$			7 10 25	V

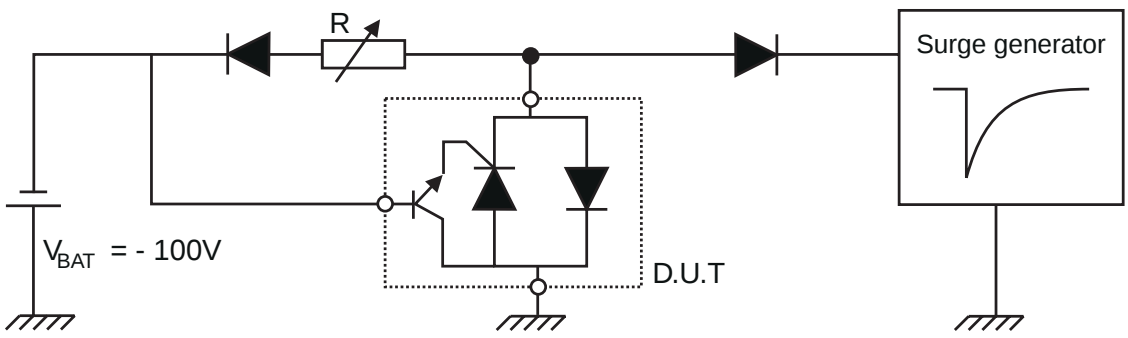
Note 2: see functional holding current (I_H) test circuitNote 3: see test circuit for V_{DGL}

The oscillations with a time duration lower than 50ns are not taken into account

3 - PARAMETERS RELATED TO DIODE AND PROTECTION THYRISTOR ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Test conditions		Typ.	Max.	Unit
I_{RM}	$V_{GATE/LINE} = -1\text{V}$ $V_{RM} = -150\text{V}$ $V_{GATE/LINE} = -1\text{V}$ $V_{RM} = -150\text{V}$	$T_c = 25^{\circ}\text{C}$ $T_c = 85^{\circ}\text{C}$		5 50	μA
C	$V_R = 50\text{V}$ bias, $V_{RMS} = 1\text{V}$, $F = 1\text{MHz}$ $V_R = 2\text{V}$ bias, $V_{RMS} = 1\text{V}$, $F = 1\text{MHz}$		30 70		pF

FUNCTIONAL HOLDING CURRENT (I_H) TEST CIRCUIT : GO-NO GO TEST



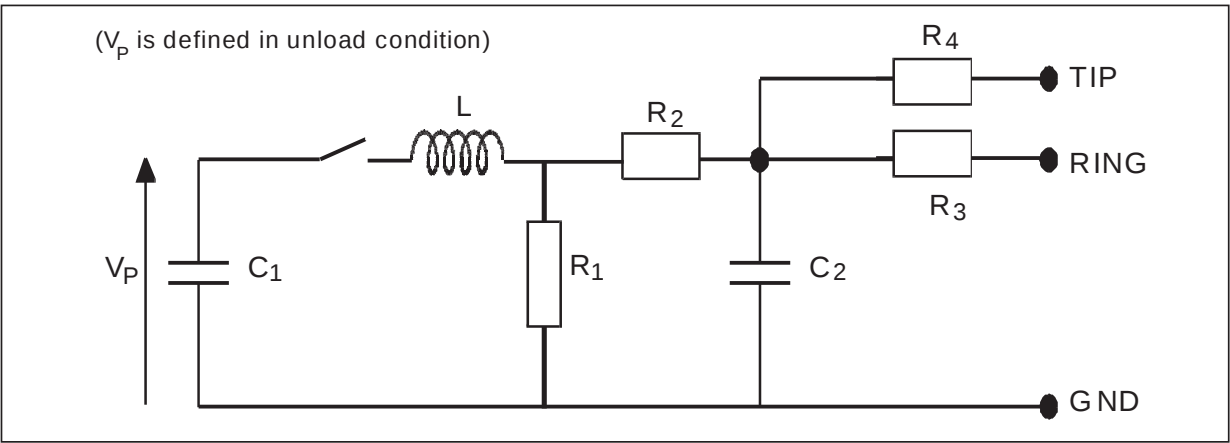
The diagram shows a test circuit for the functional holding current (I_H). A negative battery $V_{BAT} = -100V$ is connected to the base of a PNP transistor. The emitter of the transistor is connected to ground. The collector of the transistor is connected to the anode of a diode. The cathode of this diode is connected to the anode of another diode, which is connected to a variable resistor R . The other end of R is connected to the D.U.T. (Device Under Test), which is represented by a dashed box containing a diode symbol. The D.U.T. is connected to ground. A surge generator is connected to the D.U.T. and ground. The surge generator's output is shown as a pulse waveform.

This is a GO-NO GO test which allows to confirm the holding current (I_H) level in a functional test circuit.

TEST PROCEDURE :

- Adjust the current level at the I_H value by short circuiting the D.U.T.
- Fire the D.U.T. with a surge current : $I_{PP} = 10A, 10/1000\mu s$.
- The D.U.T. will come back to the off-state within a duration of 50ms max.

TEST CIRCUIT FOR V_{FP} AND V_{DGL} PARAMETERS



Pulse (μs)		V_p (V)	C_1 (μF)	C_2 (nF)	L (μH)	R_1 (Ω)	R_2 (Ω)	R_3 (Ω)	R_4 (Ω)	I_{PP} (A)	R_s (Ω)
t_r	t_p										
10	700	1500	20	200	0	50	15	25	25	30	10
1.2	50	1500	1	33	0	76	13	25	25	30	10
2	10	2500	10	0	1.1	1.3	0	3	3	38	62

TECHNICAL INFORMATION

Fig. A1: LCP1521 concept behavior.

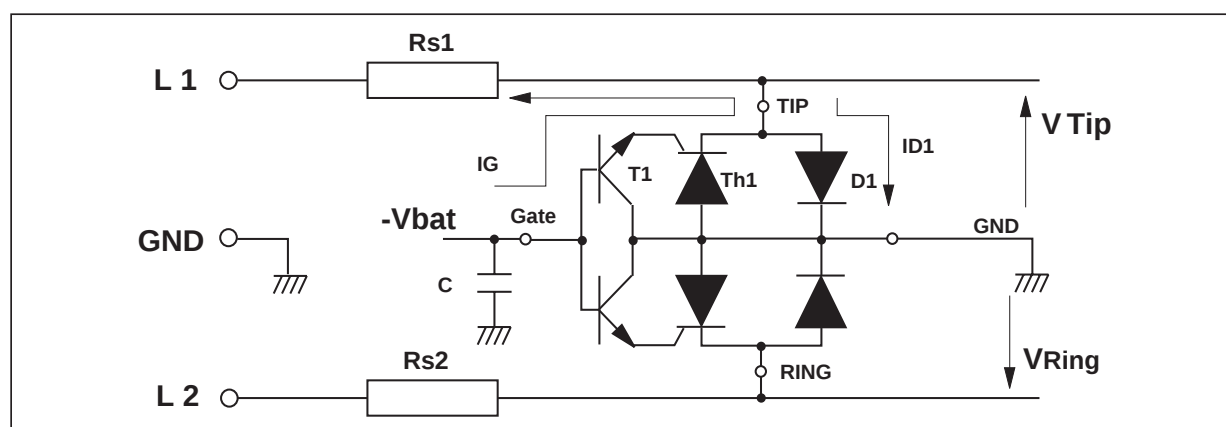
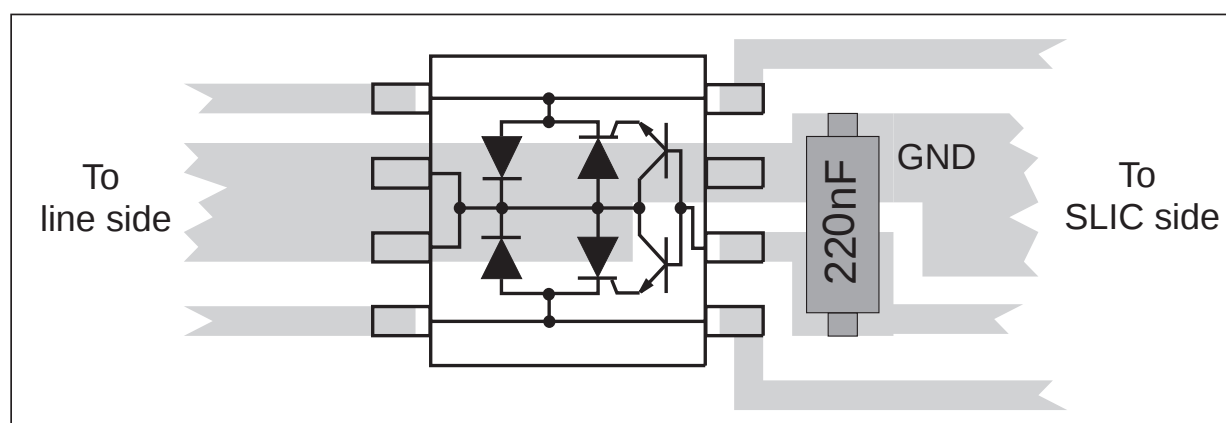


Figure A1 shows the classical protection circuit using the LCP1521 crowbar concept. This topology has been developed to protect the new high voltage SLIC's. It allows to program the negative firing threshold while the positive clamping value is fixed at GND.

When a negative surge occurs on one wire (L1 for example) a current I_G flows through the base of the transistor T1 and then injects a current in the gate of the thyristor Th1. Th1 fires and all the surge current flows through the ground. After the surge when the current flowing through Th1 becomes less negative than the holding current I_H , then Th1 switches off.

When a positive surge occurs on one wire (L1 for example) the diode D1 conducts and the surge current flows through the ground.

Fig. A2: Example of PCB layout based on LCP1521 protection.



In order to minimize the remaining voltage across the SLIC inputs during the surge, the TIP and RING pins of the LCP1521 are doubled (Pins 1 and 8 for TIP / Pins 4 and 5 for RING).

This fact allows the board designer to connect the tracks like in figure A2. With such a PCB design, the extra voltages caused by track stray inductance remain located on the line side of the LCP and do not affect the SLIC side.

The capacitor C is used to speed up the crowbar structure firing during the fast surge edges.

This allows to minimize the dynamical breakover voltage at the SLIC Tip and Ring inputs during fast strikes. Note that this capacitor is generally present around the SLIC - Vbat pin.

So to be efficient it has to be as close as possible from the LCP1521 Gate pin and from the reference ground track (or plan) (see Fig. A2). The optimized value for C is 220nF.

The series resistors Rs1 and Rs2 designed in figure A1 represent the fuse resistors or the PTC which are mandatory to withstand the power contact or the power induction tests imposed by the various country standards. Taking into account this fact the actual lightning surge current flowing through the LCP is equal to:

$$I_{\text{surge}} = V_{\text{surge}} / (R_g + R_s)$$

With V_{surge} = peak surge voltage imposed by the standard.

R_g = series resistor of the surge generator

R_s = series resistor of the line card (e.g. PTC)

e.g. For a line card with 30Ω of series resistors which has to be qualified under GR1089 Core 1000V 10/1000 μ s surge, the actual current through the LCP1521 is equal to:

$$I_{\text{surge}} = 1000 / (10 + 30) = \mathbf{25A}$$

The LCP1521 is particularly optimized for the new telecom applications such as the fiber in the loop, the WLL, the remote central office. In this case, the operating voltages are smaller than in the classical system. This makes the high voltage SLICs particularly suitable. The schematics of figure A3 gives the most frequent topology used for these applications.

Fig. A3: Protection of high voltage SLIC.

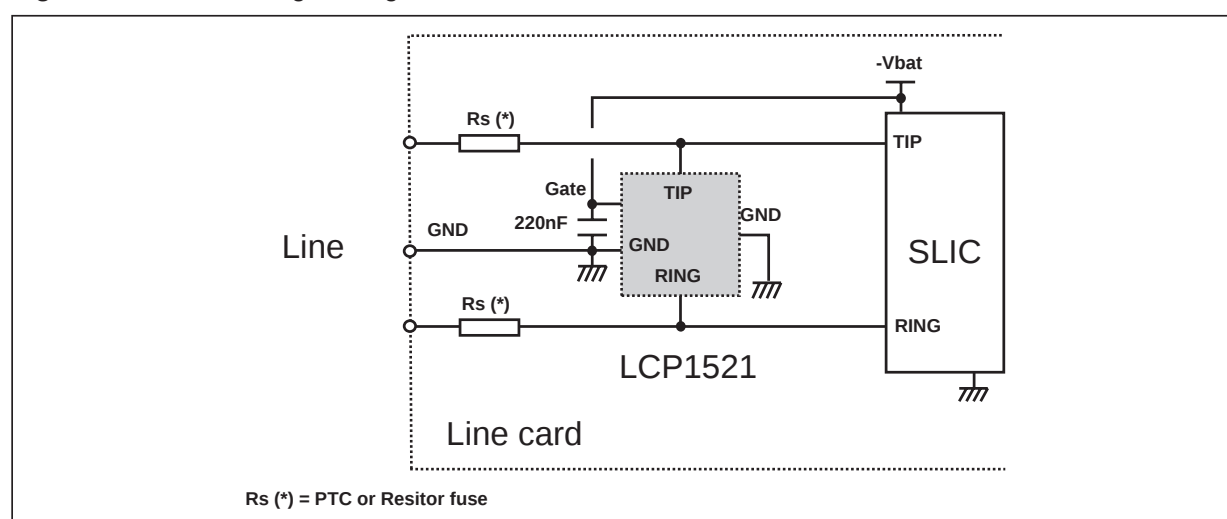


Fig. 1: Surge peak current versus overload duration.

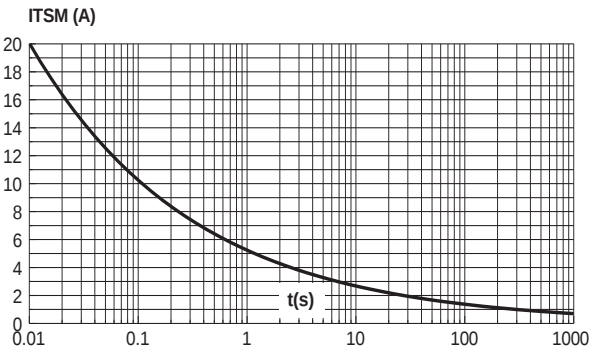
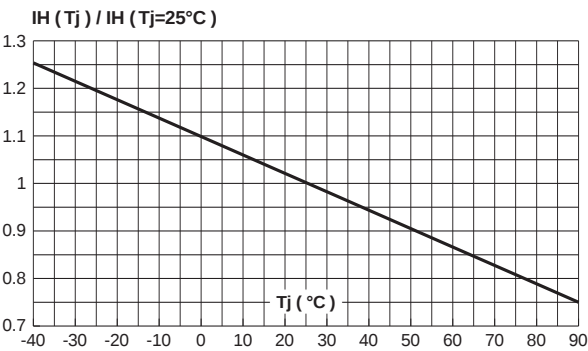
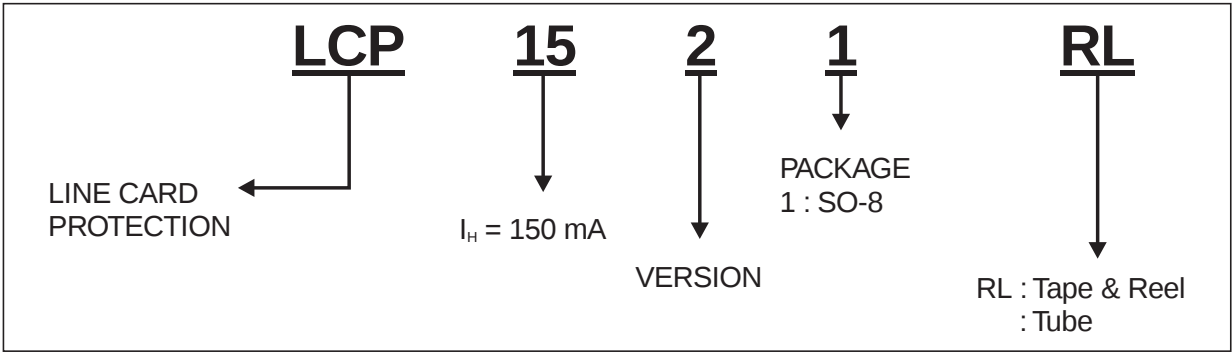


Fig. 2: Relative variation of holding current versus junction temperature

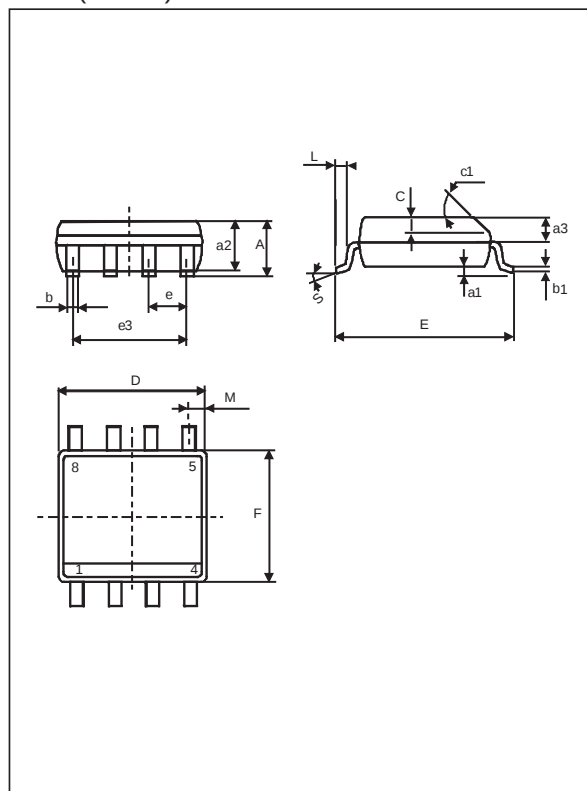


ORDER CODE



PACKAGE MECHANICAL DATA

SO-8 (Plastic)



REF.	DIMENSIONS					
	Millimetres			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C	0.25	0.50	0.50	0.010		0.020
c1	45° (typ)					
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max)					

Order code	Marking	Package	Weight	Base qty	Delivery mode
LCP1521	151DHV	SO-8	0.08 g	100	Tube
LCP1521RL	151DHV	SO-8	0.08 g	2000	Tape & Reel

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2002 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany
 Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore
 Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>